



DMP3098L

P-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

V _{(BR)DSS}	R _{DS(on) max}	I _D Τ _A = +25°C
201/	70mΩ@ V _{GS} = -10V	-3.8A
-30V	120mΩ@ V _{GS} =-4.5V	-3.0A

Features and Benefits

- Low On-Resistance
- Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

Description and Applications

This new generation MOSFET has been designed to minimize the onstate resistance ($R_{DS(on)}$) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

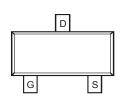
- Power management functions
- Analog Switch
- Load Switch
- Boost Switch

Mechanical Data

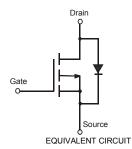
- Case: SOT23
- Case Material: Molded Plastic, "Green" Molding Compound.
 UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin annealed over Copper leadframe.
 Solderable per MIL-STD-202, Method 208
- Terminal Connections: See Diagram
- Weight: 0.008 grams (approximate)







Pin Configuration



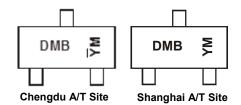
Ordering Information (Note 4)

Part Number	Case	Packaging
DMP3098L-7	SOT23	3000/Tape & Reel

Notes: 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.

- 2. See http://www.diodes.com/quality/lead_free.html com for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http://www.diodes.com/products/packages.html

Marking Information



DMB = Product Type Marking Code

YM = Date Code Marking for SAT (Shanghai Assembly/ Test site)

YM = Date Code Marking for CAT (Chengdu Assembly/ Test site)

Y or \overline{Y} = Year (ex: A = 2013) M = Month (ex: 9 = September)

Date Code Key

Year	2008		2009	2010		2011	2012		2013	2014		2015
Code	V		W	Х		Υ	Z		Α	В		С
Month	lon I	F-b	Man	A		Luna	11	A		0-4	Marr	
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec



Characteris		Symbol	Value	Units	
Drain-Source Voltage			V_{DSS}	-30	V
Gate-Source Voltage			V _{GSS}	±20	V
Drain Current (Note 5) V _{GS} = -10V	Steady State	T _A = +25°C T _A = +70°C	I _D	-3.8 -2.9	Α
Pulsed Drain Current (Note 6)			I _{DM}	-11	Α

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Units
Total Power Dissipation (Note 5)	P_{D}	1.08	W
Thermal Resistance, Junction to Ambient @T _A = +25°C (Note 5)	$R_{ hetaJA}$	115	°C/W
Operating and Storage Temperature Range	T_{J}, T_{STG}	-55 to +150	°C

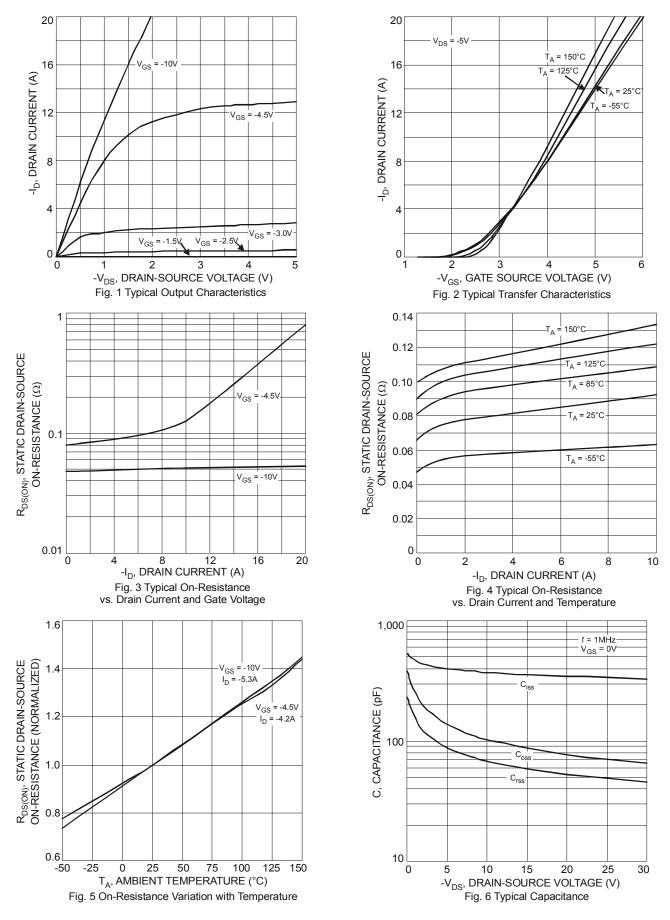
Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

01	0	141	T	Maria	1114	T4 0
Characteristic C	Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)	,		-	,		
Drain-Source Breakdown Voltage	BV _{DSS}	-30		_	V	$V_{GS} = 0V, I_D = -250\mu A$
Zero Gate Voltage Drain Current	I _{DSS}	_	_	-800	nA	$V_{DS} = -30V, V_{GS} = 0V$
Gate-Source Leakage	I _{GSS}	_	l	±100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$
ON CHARACTERISTICS (Note 7)						_
Gate Threshold Voltage	V _{GS(th)}	-1.0	-1.8	-2.1	V	$V_{DS} = V_{GS}, I_{D} = -250 \mu A$
Static Drain-Source On-Resistance	0		56	70	mΩ	$V_{GS} = -10V, I_D = -3.8A$
Static Diain-Source On-Resistance	R _{DS} (ON)	_	98	120	11122	$V_{GS} = -4.5V$, $I_D = -3.0A$
Forward Transfer Admittance	Y _{fs}	_	3.6	_	S	$V_{DS} = -5V, I_{D} = -2.7A$
Diode Forward Voltage (Note 6)	V_{SD}	_	_	-1.26	V	$V_{GS} = 0V, I_S = -2.7A$
DYNAMIC CHARACTERISTICS (Note 8)						
Input Capacitance	C _{iss}	_	336	1008	pF	
Output Capacitance	Coss	_	70	210	pF	$V_{DS} = -25V$, $V_{GS} = 0V$, $f = 1.0MHz$
Reverse Transfer Capacitance	C _{rss}	_	49	147	pF	
Gate Resistance	R_G	_	4.6	_	Ω	$V_{GS} = 0V$, $V_{DS} = 0V$, $f = 1MHz$
SWITCHING CHARACTERISTICS (Note 8)						
Total Gate Charge	Q_{g}	_	4.0	8.0		$V_{DS} = -15V$, $V_{GS} = -4.5V$, $I_{D} = -3.8A$
		_	7.8	_	nC	15)/)/ 10)/
Gate-Source Charge	Q _{gs}	_	1.0	_		$V_{DS} = -15V$, $V_{GS} = -10V$, $I_{D} = -3.8A$
Gate-Drain Charge	Q_{gd}	_	2.5	_		ID = -3.0A
Turn-On Delay Time	t _{d(on)}	_	6.0	12.0		
Rise Time	t _r	_	5.0	10.0]	$V_{DS} = -15V, V_{GS} = -10V,$
Turn-Off Delay Time	t _{d(off)}	_	17.6	35.2	ns	$I_D = -1A, R_G = 6.0\Omega$
Fall Time	t _f	_	9.5	19.0	1	

5. Device mounted on FR-4 PCB on 2 oz., 0.5 in. 2 copper pads and t \leq 5 sec. Notes:

- 6. Pulse width ≤10μS, Duty Cycle ≤1%.
 7. Short duration pulse test used to minimize self-heating effect.
 8. Guaranteed by design. Not subject to production testing.







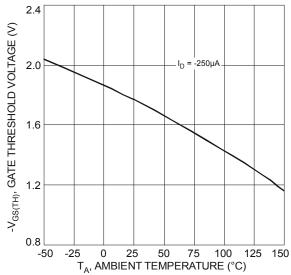
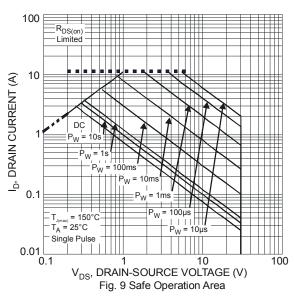
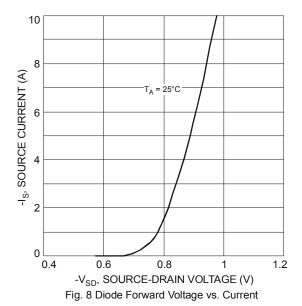


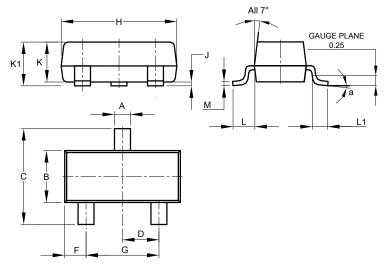
Fig. 7 Gate Threshold Variation vs. Ambient Temperature





Package Outline Dimensions

Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for latest version.

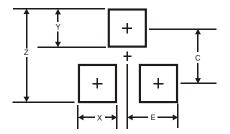


	SOT23								
Dim	Min	Max	Тур						
Α	0.37	0.51	0.40						
В	1.20	1.40	1.30						
С	2.30	2.50	2.40						
D	0.89	1.03	0.915						
F	0.45	0.60	0.535						
G	1.78	2.05	1.83						
Н	2.80	3.00	2.90						
J	0.013	0.10	0.05						
K	0.890	1.00	0.975						
K1	0.903	1.10	1.025						
L	0.45	0.61	0.55						
L1	0.25	0.55	0.40						
M	0.085	0.150	0.110						
α	α 8°								
All	All Dimensions in mm								



Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Value (in mm)				
2.9				
0.8				
0.9				
2.0				
1.35				

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